

## Product Overview

### NTH4L015N065SC1: Silicon Carbide MOSFET, N-Channel, 650V, 15.6 mΩ , TO247-4L

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

#### Features

- High Junction Temperature
- 100% UIL Tested
- RoHS Compliant
- High Speed Switching and Low Capacitance
- 650V rated
- Max RDS(on) = 18.7 mΩ at Vgs = 18V, Id = 60A

#### Benefits

- Tj = 175°C

#### Applications

- DC-DC Converter
- Boost Inverter

#### End Products

- UPS
- Solar
- Power Supply

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV <sub>DSS</sub> (V)	I <sub>D(max)</sub> (A)	R <sub>DS(on)</sub> Typ @ 25°C (mΩ)	Q <sub>g</sub> Total (C)	Output Capacitance (C)	T <sub>j</sub> Max (°C)	Package Type
NTH4L015N065SC1	15.6881	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	650	164	15.6	251	397	175	TO-247-4

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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